

# Bibliography on Applications of Scanning Probe Microscopy to Characterization of Semiconductor Materials and Surfaces

Compiled by Oleg Boldenkov, MikroMasch  
Last updated on October 2002, titles sorted in alphabetical order

**1003**

## A study comparing measurements of roughness of silicon and SiO<sub>2</sub> surfaces and interfaces using scanning probe microscopy and neutron reflectivity

A. Crossley, S.J. Sofield, M.T. Hutchings, J.P. Goff, A.C.I. Lake, A. Menelle

*Journal of Non-Crystalline Solids*, 187 (1995), 221-226

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## A study of ion-bombarded nanostructures on germanium surfaces by scanning probe microscopy

Y.J. Chen, W.Y. Cheung, I.H. Wilson, S.P. Wong, J.B. Xu

*Thin Solid Films*, 308-309 (1997), 1-4, 415-419

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## AFM analysis of sidewall formation in low angle incidence microchannel epitaxy of GaAs

A. Umeno, G. Bacchin, T. Nishinaga

*Journal of Crystal Growth*, 220 (2000), 4, 355-363

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## AFM and XPS characterization of the Si(111) surface after thermal treatment

B. Lamontagne, D. Roy, D. Guay, R. Sporken, R. Caudano

*Applied Surface Science*, 90 (1995), 4, 481-487

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## AFM characterization of PbTe quantum dots grown by molecular beam epitaxy under Volmer-Weber mode

S.O. Ferreira, B.R.A. Neves, R. Magalhaes-Paniago, A. Malachias, P.H.O. Rappl, A.Y. Ueta, E. Abramof, M.S. Andrade

*Journal of Crystal Growth*, 231 (2001), 1-2, 121-128

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## AFM fabrication and characterization of InAs/AlGaSb nanostructures

T. Ikeda, A. Kajiuchi, S. Sasa, M. Inoue

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## AFM measurement of initially grown GaN layer on GaAs substrate

H. Tanaka, A. Nakadaira

*Journal of Crystal Growth*, 221 (2000), 1-4, 271-275

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## AFM observation of Si/SiO<sub>2</sub> interface subjected to electric stress

M. Inoue, A. Shimada, J. Shirafuji

*Applied Surface Science*, 117-118 (1997) 187-191

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## AFM studies of hydrogen implanted silicon

A. Piatkowska, J. Jagielski, G. Gawlik

*Applied Surface Science*, 141 (1999), 3-4, 333-338

**104****AFM study and optical properties of GaAsN/GaAs epilayers grown by MOVPE**

L. Auvray, H. Dumont, J. Dazord, Y. Monteil, J. Bouix, C. Bru-Chevalier

*Journal of Crystal Growth, 221 (2000), 1-4, 475-480***183****AFM study of lattice matched and strained InGaAsN layers on GaAs**

Y. Park, M.J. Cich, R. Zhao, P. Specht, H. Feick, E.R. Weber

*Physica B: Condensed Matter, 308-310 (2001), 98-101***171****AFM study of swift gold ion irradiated silicon**

P.C. Srivastava, V. Ganesan, O.P. Sinha

*Nuclear Instruments and Methods in Physics Research Section B:**Beam Interactions with Materials and Atoms, 187 (2002), 220-230***247****AFM tip induced selective electrochemical etching of and metal deposition on p-GaAs(100) surface**

K. Uosaki, M. Koinuma

*Surface Science, 357-358 (1996), 565-570***182****AFM-based fabrication of Si nanostructures**

P.M. Campbell, E.S. Snow, P.J. McMarr

*Physica B: Condensed Matter, 227 (1996), 1-4, 315-317***239****An AFM study of the processing of hydrogen passivated silicon(111) of a low miscut angle**

D.A. MacLaren, N.J. Curson, P. Atkinson, W. Allison

*Surface Science, 490 (2001), 3, 285-295***310****An atomic force microscopy study of a temperature dependent morphology transition of GaN grown on sapphire by MOCVD**

P.K. Larsen, P.R. Hageman, A.R.A. Zauner, W.J.P. Van Enckevort, F.K. de Theije

*Journal of Crystal Growth, 197 (1999), 1-2, 37-47***96****An electrochemical AFM study on electrodeposition of copper on p-GaAs(100) surface in HCl solution**

M. Koinuma, K. Uosaki

*Electrochimica Acta, 40 (1995), 10, 1345-1351***342****Atomic force microscopy and scanning tunneling microscopy studies on the growth mechanism of a-Si:H film on graphite substrate**

M. Matsuse, S. Tsuboi, T. Arakane, M. Kawasaki, H. Koinuma

*Journal of Non-Crystalline Solids, 198-200 (1996), 787-791***361****Atomic force microscopy investigation of dislocation structures and deformation characteristics in neutron-irradiated silicon detectors**

G. Golan, E. Rabinovich, A. Inberg, M. Oksman, P.G. Rancoita, M. Rattaggi, K. Gartsman, A. Seidman, N. Croitoru

*Microelectronics Journal, 31 (2000), 11-12, 937-944*

**386****Atomic force microscopy on bare and thiol monolayer covered gallium arsenide**

A. Abdelghani

*Materials Letters, 50 (2001), 2-3, 73-77***389****Atomic force microscopy on SiO<sub>2</sub> layers grown on Ge implanted silicon**

V. Raineri, S. Lombardo, F. Iacona, F. La Via

*Nuclear Instruments and Methods in Physics Research Section B:**Beam Interactions with Materials and Atoms, 116 (1996), 1-4, 482-485***394****Atomic force microscopy studies of substrate cleaning using tris(dimethylamino)arsenic and tris(dimethylamino)antimony and investigations of surface decomposition mechanisms**

T.J. Whitaker, T. Martin, A.D. Johnson, A.J. Pidduck, J.P. Newey

*Journal of Crystal Growth, 164 (1996), 1-4, 125-131***403****Atomic force microscopy study of FG-annealed and PECVD silicon nitride Ar-coated silicon solar cells**

R. Koshore, H.R. Moutinho, B.L. Sopori

*Renewable Energy, 6 (1995), 5-6, 589-591***404****Atomic force microscopy study of morphology and dislocation structure of InAs and GaSb grown on highly mismatched substrates**

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*Journal of Crystal Growth, 170 (1997), 1-4, 788-793***415****Atomic force microscopy study of ZnSe/GaAs heteroepitaxy processes by metalorganic vapour phase epitaxy**

K. Uesugi, H. Suzuki, H. Nashiki, T. Obinata, I. Suemune, H. Kumano, J. Nakahara

*Applied Surface Science, 113-114 (1997), 371-376***417****Atomic force microscopy study on the surface structure of oxidized porous silicon**

T.F. Young, I.W. Huang, Y.L. Yang, W.C. Kuo, I.M. Jiang, C.Y. Chang, T.C. Chang

*Applied Surface Science, 102 (1996), 404-407***429****Atomic scale properties of interior interfaces of semiconductor heterostructures as determined by quasi-digital highly selective etching and atomic force microscopy**

R. Rettig, W. Stolz

*Physica E: Low-dimensional Systems and Nanostructures, 2 (1998), 1-4, 277-281***128****Atomic structure of bare p-GaAs(100) and electrodeposited Cu on p-GaAs(100) surfaces in H<sub>2</sub>SO<sub>4</sub> solutions: an AFM study**

M. Koinuma, K. Uosaki

*Journal of Electroanalytical Chemistry, 409 (1996), 1-2, 45-50***110****Atomically flat OMVPE growth of GaInAs and InP observed by AFM for level narrowing in resonant tunneling diodes**

M. Suhara, C. Nagao, H. Honji, Y. Miyamoto, K. Furuya, R. Takemura

*Journal of Crystal Growth, 179 (1997), 1-2, 18-25*

**433****Atomistic comparative study of VUV photodeposited silicon nitride on InP(100) by simulation and atomic force microscopy**

Z. Wang, J. Marquez, C. David, J.F. Palmier, J. Flicstein, E. Guillonneau, J.L. Courant, L.S. How Kee Chun, D. Maisonneuve

*Applied Surface Science, 154-155 (2000), 337-344*

**434****Atomistic comparative study of VUV photodeposited silicon nitride on InP(100) by simulation and atomic force microscopy: discrete representation and topological analysis**

J. Flicstein, E. Guillonneau, J. Marquez, L.S. How Kee Chun, D. Maisonneuve, C. David, Z.Z. Wang, J.F. Palmier, J.L. Courant

*Computational Materials Science, 17 (2000), 2-4, 525-533*

**109****Behaviour of vicinal InP surfaces grown by MOVPE: Exploitation of AFM images**

H. Dumont, V. Thevenot, V. Souliere, Y. Monteil, J. Bouix, P. Regreny, T.-M. Duc

*Journal of Crystal Growth, 170 (1997), 1-4, 251-256*

**439****Catalyst genesis studied by atomic force microscopy**

R.M. Lambert, C.M.C. de Castilho, D.P.C. Bird

*Surface Science, 449 (2000), 1-3, L221-L227*

**821****Characterization of asymmetric fragmentation patterns in SFM images of porous silicon**

I. Pepe, A. Ferreira da Silva, R.R. Rosa, L.S. Roman, E. Veje

*Solid State Communications, 113 (2000), 12, 703-708*

**448****Characterization of self-assembled Ge islands on Si(100) by atomic force microscopy and transmission electron microscopy**

K. Eberl, G. Wohl, C. Schollhorn, O.G. Schmidt, O. Kienzle, K. Brunner, F. Ernst

*Thin Solid Films, 321 (1998), 1-2, 86-91*

**215****Characterization of silicon transducers with Si<sub>3</sub>N<sub>4</sub> sensing surfaces by an AFM and a PAB system**

M. Adami, D. Alliata, C. Del Carlo, M. Martini, L. Piras, M. Sartore, C. Nicolini

*Sensors and Actuators B: Chemical, 25 (1995), 1-3, 889-893*

**46****Chemical interactions in noncontact AFM on semiconductor surfaces: Si(111), Si(100) and GaAs(110)**

I. Stich, R. Perez, K. Terakura, M.C. Payne

*Applied Surface Science, 140 (1999), 3-4, 320-326*

**456****Comparative study of polysilicon-on-oxide using spectroscopic ellipsometry, atomic force microscopy, and transmission electron microscopy**

M. Fried, T. Lohner, L.P. Bro, C. Schneider, R. Berger, J. Gyulai, H. Ryssel, P. Petrik

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**Comparative study of the GaAs (113), (115), (001), (115), (113), and (110) surfaces by atomic force microscopy, low energy electron diffraction, and reflectance anisotropy spectroscopy**

N. Esser, W. Richter, M. Pristovsek, H. Menhal, T. Schmidling

*Microelectronics Journal*, 30 (1999), 4-5, 449-453

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**Composition dependence of surface morphology of ultrathin a-SiGe:H alloys studying by atomic force microscopy**

S. Miyazaki, K. Chen, M. Hirose, D. Feng, J. Xu

*Thin Solid Films*, 335 (1998), 1-2, 130-133

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**Confirmation of immobilizing IgG on different surfaces with AFM and impedance investigations of a Pt electrode during the immobilization**

C.-D. Feng, J.R. Stetter, Y.-D. Ming, P.J. Hesketh, S.M. Gendel

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M. Guggisberg, O. Pfeiffer, S. Schar, V. Barwick, M. Bammerlin, C. Loppacher, R. Bennewitz, A. Baratoff, E. Meyer

*Applied Physics A: Materials Science & Processing*, 72 (2001), 7, S19-S22

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**Cross section potentiometry of doped silicon structures using SFM**

A. Breymesser, V. Schlosser, J. Summhammer

*Physica Status Solidi B - Basic Research*, 215 (1999), 1, 855-858

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**Cross-sectional atomic force microscopy of ZnMgSSe and BeMgZnSe-based laser diodes**

A. V. Ankudinov, A. N. Titkov, T. V. Shubina, S. V. Ivanov, P. S. Kop'ev, H.-J. Lugauer, G. Reuscher, M. Keim, A. Waag, and G. Landwehr

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D. Sarid, C.A. Peterson, R.K. Workman

*Surface Science*, 423 (1999), 2-3, L277-L279

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**Direct observation of the transition from a 2D layer to 3D islands at the initial stage of InGaAs growth on GaAs by AFM**

M. Kitamura, M. Nishioka, R. Schur, Y. Arakawa

*Journal of Crystal Growth*, 170 (1997), 1-4, 563-567

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Y. Sugawara, T. Tsukamoto, T. Minobe, Shigeki Orisaka, S. Morita, T. Uchihashi

*Applied Surface Science*, 140 (1999), 3-4, 298-303

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**Effect of the substrate on the structural properties of low temperature microcrystalline silicon films - a Raman spectroscopy and atomic force microscopy investigation**

E.A.T. Dirani, A.M. Andrade, L.K. Noda, F.J. Fonseca, P.S. Santos

*Journal of Non-Crystalline Solids*, 273 (2000), 1-3, 307-313

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**Electrical characterization of semiconductor materials and devices using scanning probe microscopy**

P. De Wolf, E. Brazel, A. Erickson

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L. Bolotov, N. Uchida, T. Kanayama

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**Evolution of strained Ge islands grown on Si(111): a scanning probe microscopy study**

G. Capellini, A. Sgarlata, N. Motta, R. Calarco

*Solid State Communications*, 112 (1999), 3, 145-149

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**Feasibility of the electrical characterization of single SiO<sub>2</sub> breakdown spots using C-AFM**

M. Porti, R. Rodriguez, M. Nafra, X. Aymerich, A. Olbrich, B. Ebersberger

*Journal of Non-Crystalline Solids*, 280 (2001), 1-3, 138-142

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**First stages of platinum electroless deposition on silicon(100) from hydrogen fluoride solutions studied by AFM**

P. Gorostiza, J. Servat, F. Sanz

*Thin Solid Films*, 275 (1996), 1-2, 12-17

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**Formation and stability of II-VI self-assembled quantum dots revealed by in situ atomic force microscopy**

P.R. Kratzert, M. Rabe, F. Henneberger

*Applied Surface Science*, 166 (2000), 1-4, 332-335

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A. Howie, M.R. Castell, D.A. Ritchie

*Acta Materialia*, 46 (1998), 2, 579-584

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**GaN films studied by near-field scanning optical microscopy, atomic force microscopy and high resolution X-ray diffraction**

T.F. Kuech, J. Liu, D. Zhi, J.M. Redwing, M.A. Tischler

*Journal of Crystal Growth*, 170 (1997), 1-4, 357-361

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**Growth of zinc sulfide thin films on (100)Si with the successive ionic layer adsorption and reaction method studied by atomic force microscopy**

M. Leskela, G. Friedbacher, M. Grasserbauer, M.P. Valkonen, R. Resch, S. Lindroos

*Applied Surface Science*, 136 (1998), 1-2, 131-136

**45****Imaging of chemical reactivity and buckled dimers on Si(100)2x1 reconstructed surface with noncontact AFM**

T. Tsukamoto, T. Okada, T. Minobe, Y. Sugawara, T. Uchihashi, S. Orisaka, S. Morita  
*Applied Surface Science*, 140 (1999), 3-4, 304-308

**537****Imaging silicon by atomic force microscopy with crystallographically oriented tips**

F.J. Giessibl, S. Hembacher, H. Bielefeldt, J. Mannhart

*Applied Physics A: Materials Science & Processing*, 72 (2001), 7, S15-S17

**541****Improved heterointerface quality of V-shaped AlGaAs/GaAs quantum wires characterized by atomic force microscopy and micro-photoluminescence**

X.-L. Wang, V. Voliotis, R. Grousson, M. Ogura

*Journal of Crystal Growth*, 213 (2000), 1-2, 19-26

**107****Improvement of nanoscale patterning of heavily doped p-type GaAs by atomic force microscope (AFM)-based surface oxidation process**

A. Yamada, M. Konagai, Y. Matsuzaki

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**549****In situ ellipsometry and atomic force microscopy study of the initial stage of hydrogenated silicon growth**

T. Arai, H. Shirai, T. Nakamura

*Journal of Non-Crystalline Solids*, 227-230 (1998), 53-58

**101****In situ RHEED and AFM investigation of growth front morphology evolution of Si(001) grown by UHV-CVD**

S. Nayak, D.E. Savage, H.-N. Chu, M.G. Lagally, T.F. Kuech

*Journal of Crystal Growth*, 157 (1995), 1-4, 168-171

**120****In situ RHEED, AFM, and REM investigations of the surface recovery of MBE-grown GaAs(001)-layers during growth interruptions**

R. Anton, P. Kreutzer, W. Naumann, T. Franke, T. Zacher

*Journal of Crystal Growth*, 193 (1998), 4, 451-459

**191****InAs/AlGaSb nanoscale device fabrication using AFM oxidation process**

M. Inoue, C. Dohno, S. Sasa, T. Ikeda

*Physica E: Low-dimensional Systems and Nanostructures*, 2 (1998), 1-4, 858-861

**557****In-situ atomic force microscopy of silicon(100) in aqueous potassium hydroxide**

P. Raisch, W. Haiss, R.J. Nichols, D.J. Schiffrin

*Electrochimica Acta*, 45 (2000), 28, 4635 - 4643

**866****Kelvin probe measurements of microcrystalline silicon on a nanometer scale using SFM**

A. Breymesser, V. Schlosser, D. Peiro, C. Voz, J. Bertomeu, J. Andreu, J. Summhammer

*Solar Energy Materials & Solar Cells*, 66 (2001), 1-4, 171-177

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**Local electronic transport in microcrystalline silicon observed by combined atomic force microscopy**

A. Fejfar, B. Rezek, P. Knapk, J. Stuchlk, J. Kocka

*Journal of Non-Crystalline Solids, 266-269 (2000), 309-314*

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**Local surface band modulation with MBE-grown InAs quantum dots measured by atomic force microscopy with conductive tip**

I. Kamiya, I. Tanaka, H. Sakaki

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**Low temperature growth of Si on Si(111) by gas-source MBE with rapid thermal annealing: AFM study on surface morphology**

H. Okumura, M. Sano, T. Akane, S. Matsumoto, T. Ishikawa

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**Measurement of induced surface charges, contact potentials, and surface states in GaN by electric force microscopy**

P. M. Bridger, Z. Z. Bandic, E. C. Piquette, T. C. McGill

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**Micromorphology changes of silicon oxide on Si(111) during current oscillations: a comparative in situ AFM and FTIR study**

H.-J. Lewerenz, H. Jungblut, S. Rauscher, O. Nast

*Journal of Electroanalytical Chemistry, 442 (1998), 1-2, 169-174*

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**Morphological study by XPS and AFM of wide band gap  $\beta$ -In<sub>2</sub>S<sub>3</sub> thin films synthesized by a dry physical process**

N. Barreau, S. Marsillac, J. C. Bernede, L. Assmann, V. Jousseau

*Journal of Materials Science: Materials in Electronics, 13 (2002), 2, 95-100*

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**MOVPE growth of GaAsN: surface study by AFM and optical properties**

L. Auvray, H. Dumont, J. Dazord, Y. Monteil, J. Bouix, C. Bru-Chevallier, L. Grenouillet

*Materials Science in Semiconductor Processing, 3 (2000), 5-6, 505-509*

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**Nanofabrication of heavily doped p-type GaAs and n-type InGaP by atomic force microscope (AFM)-based surface oxidation process**

J.-i. Shirakashi, Y. Matsuzaki, K.-i. Yuasa, M. Konagai, E.K. Chilla, A. Yamada

*Journal of Crystal Growth, 201-202 (1999) 656-659*

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**Nano-scale potential profiles of silicon particle detectors measured by atomic force microscopy**

A. Ruzin, N. Croitoru, G. Lubarsky, Y. Rosenwaks

*Nuclear Instruments and Methods in Physics Research Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 461 (2001), 1-3, 229-232*

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J.L. Hansen, S. Tougaard, A.C. Simonsen, A.N. Larsen, M. Schleberger

*Thin Solid Films, 338 (1999), 1-2, 165-171*

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**New method based on atomic force microscopy for in-depth characterization of damage in Si irradiated with 209 MeV Kr**

L.P. Biro, J. Gyulai, S. Bogen, L. Frey, H. Ryssel, K. Havancsak, A.Y. Didyk

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Y. Sugawara, S. Orisaka, E. Hidaka, S. Morita

*Applied Physics A: Materials Science & Processing, 72 (2001), 7, S11-S14*

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**Noncontact AFM imaging on Al-adsorbed Si(111) surface with an empty orbital**

Y. Sugawara, S. Orisaka, S. Morita

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**Nucleation and growth analysis of microcrystalline silicon by scanning probe microscopy: substrate dependence, local structural and electronic properties of as-grown surfaces**

C. Ross, J. Herion, H. Wagner

*Journal of Non-Crystalline Solids, 266-269 (2000), 69-73*

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**Observation of Structural Depth Profiles in Porous Silicon by Atomic Force Microscopy**

D.C. Chang, V. Baranauskas, I. Doi, T. Prohaska

*Journal of Porous Materials, 7 (2000), 1/3, 349-352*

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**On the roughness of ideally planar H-Si(111) surfaces. An atomic force microscopy approach**

P. Dumas, F. Salvan, M. Ramonda

*Surface Science, 411 (1998), 1-2, L839-L843*

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**Piezoresistive sensors on AFM cantilevers with atomic resolution**

R. Jumperz, O. Ohlsson, A.v.d. Hart, J. Schelten, F. Saurenbach

*Microelectronic Engineering, 41-42 (1998) 441-444*

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**Propagation of the SiO<sub>2</sub> breakdown event on MOS structures observed with conductive atomic force microscopy**

M. Porti, M. Nafra, X. Aymerich, A. Olbrich, B. Ebersberger

*Microelectronic Engineering, 59 (2001), 1-4, 265-269*

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**Raman scattering study and AFM morphological characterization of MOVPE-grown (111)-strained heterostructures**

S. Gennari, G. Attolini, C. Pelosi, P.P. Lottici, F. Ricco, M. Labardi, M. Allegrini, C. Frediani

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**Roughness and chemistry of silicon and polysilicon surfaces etched in high-density plasma: XPS, AFM and ellipsometry analysis**

L. Rolland, C. Vallee, M.-C. Peignon, C. Cardinaud

*Applied Surface Science, 164 (2000), 1-4, 147-155*

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**Rutherford backscattering spectrometry, particle induced X-ray emission and atomic force microscopy of InAs thin films grown on GaAs: A complementary study**

T. Bouhacina, J.P. Aime, A.S. Barriere, H. Guegan, N. Grandjean, J. Massies  
*Thin Solid Films*, 278 (1996), 1-2, 155-165

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**Scanning force microscopy investigation of ion bombarded InP**

C.M. Demanet

*Applied Surface Science*, 135 (1998), 1-4, 53-58

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**Semiconductor acousto-electric potential detection using a force microscope**

S. Hosaka, A. Kikukawa

*Applied Surface Science*, 140 (1999), 3-4, 394-399

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K. Morimoto, K. Araki, K. Yamashita, K. Morita, M. Niwa

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F. Chollet, E. Andre, W. Vandervorst, M. Caymax

*Journal of Crystal Growth*, 157 (1995), 1-4, 161-167

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**Simulated nc-AFM images of Si(001) surface with nanotube tip**

K. Tagami, N. Sasaki, M. Tsukada

*Applied Surface Science*, 172 (2001), 3-4, 301-306

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**Simulated Noncontact Atomic Force Microscopy Images of Si(001) Surface with Silicon Tip**

K. Tagami and M. Tsukada

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**Simultaneous imaging of the In and As sublattice on InAs(110)-(1x1) with dynamic scanning force microscopy**

A. Schwarz, R. Wiesendanger, U.D. Schwarz, W. Allers

*Applied Surface Science*, 140 (1999), 3-4, 293-297

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**Simultaneous imaging of tunneling current and damping energy by noncontact-AFM in ultra-high vacuum**

T. Arai, M. Tomitori

*Applied Physics A: Materials Science & Processing*, 72 (2001), 7, S51-S54

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**Single ion impacts on an In<sub>0.22</sub>Ga<sub>0.78</sub>As/GaAs(100) surface observed by atomic force microscopy**

I.H. Wilson, Y.J. Chen, J.B. Xu

*Nuclear Instruments and Methods in Physics Research Section B: Beam Interactions with Materials and Atoms*, 124 (1997), 4, 500-505

**700****Site discrimination of adatoms in Si(111)-7 x 7 by noncontact atomic force microscopy**

N. Nakagiri, K. Okiguchi, H. Sugimura, M. Suzuki

*Surface Science, 373 (1997), 1, 1329-1332***704****Strain mapping of V-groove InGaAs/GaAs strained quantum wires using cross-sectional Atomic Force Microscopy**

F. Lelarge, C. Priester, C. Constantin, A. Rudra, K. Leifer, E. Kapon

*Applied Surface Science, 166 (2000), 1-4, 290-294***705****Strain relaxation onset in In<sub>0.08</sub>Ga<sub>0.92</sub>As/GaAs multiple-quantum wells investigated by high-resolution X-ray diffraction and atomic force microscopy**

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*Applied Surface Science, 115 (1997), 3, 211-216***226****Structural studies of sulfur-passivated GaAs (100) surfaces with LEED and AFM**

Y. Darici, N. Tao, X.W. Wang, Y. Ke, S. Milano

*Surface Science, 415 (1998), 1-2, 29-36***713****Structural study of electrochemically deposited copper on p-GaAs(001) by atomic force microscopy and surface X-ray absorption fine structure measurement**

T. Kondo, M. Koinuma, K. Uosaki, H. Oyanagi, K. Tamura

*Applied Surface Science, 121-122 (1997), 102-106***731****Surface morphology studies on sublimation grown GaN by atomic force microscopy**

R.S. Qhalid Fareed, S. Sakai, S. Tottori, K. Nishino

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